

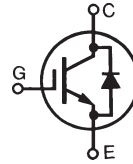
BiMOSFET™ Monolithic Bipolar MOS Transistor

IXBK75N170 IXBX75N170

$$V_{CES} = 1700V$$

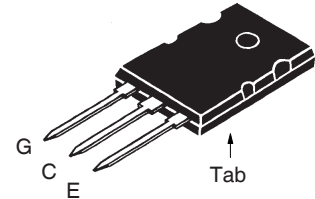
$$I_{C110} = 75A$$

$$V_{CE(sat)} \leq 3.1V$$

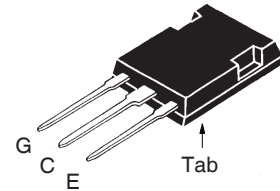


Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ C$ to $150^\circ C$	1700	V
V_{CGR}	$T_J = 25^\circ C$ to $150^\circ C$, $R_{GE} = 1M\Omega$	1700	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ C$ (Chip Capability)	200	A
I_{LRMS}	$T_C = 25^\circ C$ (Lead RMS Limit)	160	A
I_{C110}	$T_C = 110^\circ C$	75	A
I_{CM}	$T_C = 25^\circ C$, 1ms	580	A
SSOA	$V_{GE} = 15V$, $T_{VJ} = 125^\circ C$, $R_G = 1\Omega$	$I_{CM} = 150$	A
(RBSOA)	Clamped Inductive Load	$V_{CE} \leq 0.8 \cdot V_{CES}$	
P_C	$T_C = 25^\circ C$	1040	W
T_J		-55 ... +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		-55 ... +150	$^\circ C$
T_L	Maximum Lead Temperature for Soldering	300	$^\circ C$
T_{SOLD}	1.6 mm (0.062 in.) from Case for 10	260	$^\circ C$
M_d	Mounting Torque (TO-264)	1.13/10	Nm/lb.in.
F_c	Mounting Force (PLUS247)	20..120/4.5..27	N/lb.
Weight	TO-264	10	g
	PLUS247	6	g

TO-264 (IXBK)



PLUS247™ (IXBX)



G = Gate C = Collector
E = Emitter Tab = Collector

Features

- International Standard Packages
- High Blocking Voltage
- High Current Handling Capability
- Anti-Parallel Diode

Advantages

- High Power Density
- Low Gate Drive Requirement
- Intergrated Diode Can Be Used for Protection

Applications

- Capacitor Discharge
- AC Switches
- Switch-Mode and Resonant-Mode Power Supplies
- UPS
- AC Motor Drives

Symbol	Test Conditions ($T_J = 25^\circ C$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 250\mu A$, $V_{GE} = 0V$	1700		V
$V_{GE(th)}$	$I_C = 1.5mA$, $V_{CE} = V_{GE}$	2.5		5.5 V
I_{CES}	$V_{CE} = 0.8 \cdot V_{CES}$, $V_{GE} = 0V$ $T_J = 125^\circ C$			25 μA 2 mA
I_{GES}	$V_{CE} = 0V$, $V_{GE} = \pm 20V$			± 100 nA
$V_{CE(sat)}$	$I_C = I_{C110}$, $V_{GE} = 15V$, Note 1 $T_J = 125^\circ C$	2.6 3.1	3.1	V V

Symbol Test Conditions

($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)

Characteristic Values

Symbol	Test Conditions	Min.	Typ.	Max.	Units
g_{fs}	$I_C = I_{C110}, V_{CE} = 10V$, Note 1	34	56		S
C_{ies}	$V_{CE} = 25V, V_{GE} = 0V, f = 1\text{MHz}$		6930		pF
C_{oes}			400		pF
C_{res}			150		pF
Q_g	$I_C = I_{C110}, V_{GE} = 15V, V_{CE} = 0.5 \cdot V_{CES}$		350		nC
Q_{ge}			50		nC
Q_{gc}			160		nC
$t_{d(on)}$	Resistive load, $T_J = 25^\circ\text{C}$		46		ns
t_r		$I_C = I_{C110}, V_{GE} = 15V$		160	
$t_{d(off)}$	$R_G = 1\Omega, V_{CE} = 0.5 \cdot V_{CES}$		260		ns
t_f				440	
$t_{d(on)}$	Resistive load, $T_J = 125^\circ\text{C}$		47		ns
t_r		$I_C = I_{C110}, V_{GE} = 15V$		230	
$t_{d(off)}$	$R_G = 1\Omega, V_{CE} = 0.5 \cdot V_{CES}$		260		ns
t_f				580	
R_{thJC}				0.12	$^\circ\text{C/W}$
R_{thCS}		0.15			$^\circ\text{C/W}$

Reverse Diode

Symbol Test Conditions

($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)

Characteristic Values

Symbol	Test Conditions	Min.	Typ.	Max.	Units
V_F	$I_F = I_{C110}, V_{GE} = 0V$, Note 1			3.0	V
t_{rr}	$I_F = 37A, V_{GE} = 0V, -di_F/dt = 100A/\mu\text{s}$		1.5		μs
I_{RM}			50		A
Q_{RM}		$V_R = 100V, V_{GE} = 0V$		38.2	

Note

1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

Additional provisions for lead-to-lead isolation are required at $V_{CE} > 1200V$.

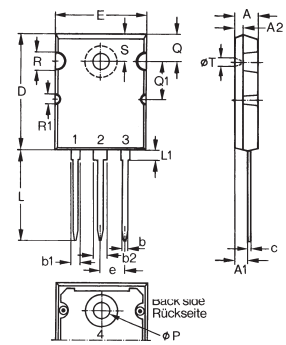
PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

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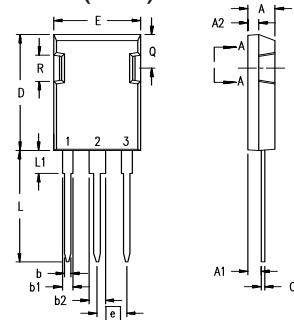
IXYS MOSFETs and IGBTs are covered 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585 7,005,734 B2 7,157,338 B2
by one or more of the following U.S. patents: 4,850,072 5,017,508 5,063,307 5,381,025 6,259,123 B1 6,534,343 6,710,405 B2 6,759,692 7,063,975 B2
4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2 7,071,537

TO-264 AA (IXBK) Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.82	5.13	.190	.202
A1	2.54	2.89	.100	.114
A2	2.00	2.10	.079	.083
b	1.12	1.42	.044	.056
b1	2.39	2.69	.094	.106
b2	2.90	3.09	.114	.122
c	0.53	0.83	.021	.033
D	25.91	26.16	1.020	1.030
E	19.81	19.96	.780	.786
e	5.46 BSC		.215 BSC	
J	0.00	0.25	.000	.010
K	0.00	0.25	.000	.010
L	20.32	20.83	.800	.820
L1	2.29	2.59	.090	.102
P	3.17	3.66	.125	.144
Q	6.07	6.27	.239	.247
Q1	8.38	8.69	.330	.342
R	3.81	4.32	.150	.170
R1	1.78	2.29	.070	.090
S	6.04	6.30	.238	.248
T	1.57	1.83	.062	.072

PLUS247™ (IXBX) Outline



Terminals: 1 - Gate
2 - Drain (Collector)
3 - Source (Emitter)

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	.190	.205
A ₁	2.29	2.54	.090	.100
A ₂	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b ₁	1.91	2.13	.075	.084
b ₂	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	0.244
R	4.32	4.83	.170	.190

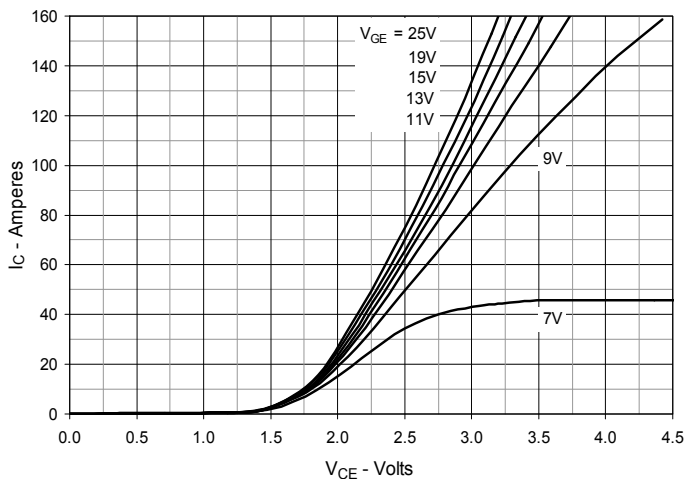
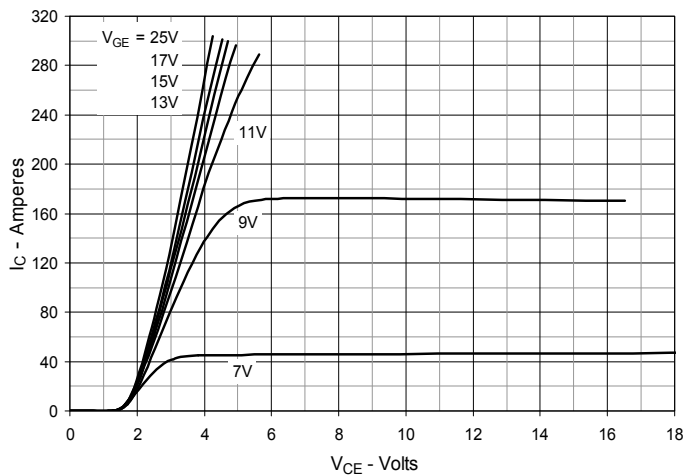
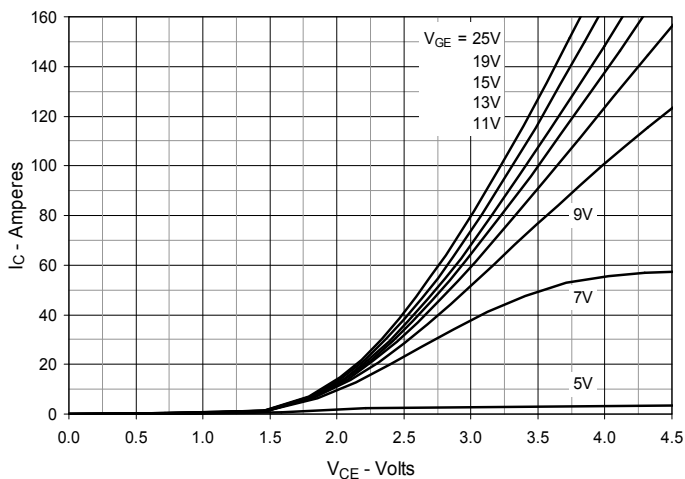
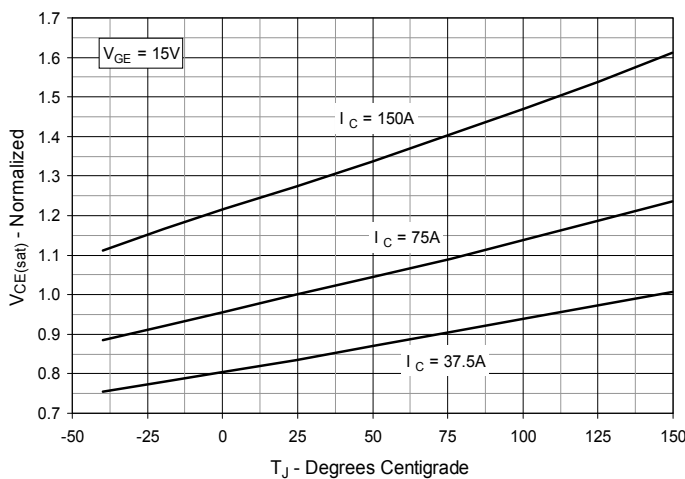
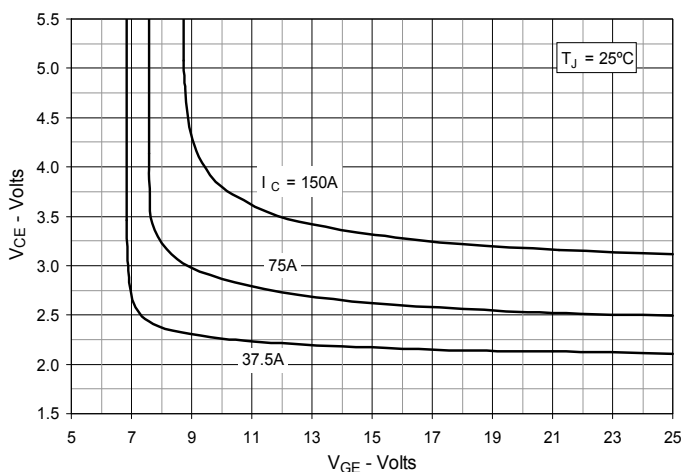
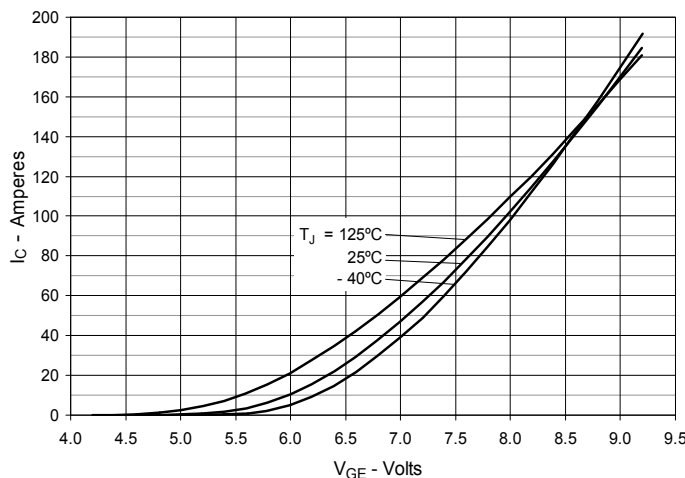
**Fig. 1. Output Characteristics
@ 25°C**

**Fig. 2. Extended Output Characteristics
@ 25°C**

**Fig. 3. Output Characteristics
@ 125°C**

**Fig. 4. Dependence of $V_{CE(sat)}$ on
Junction Temperature**

**Fig. 5. Collector-to-Emitter Voltage
vs. Gate-to-Emitter Voltage**

Fig. 6. Input Admittance


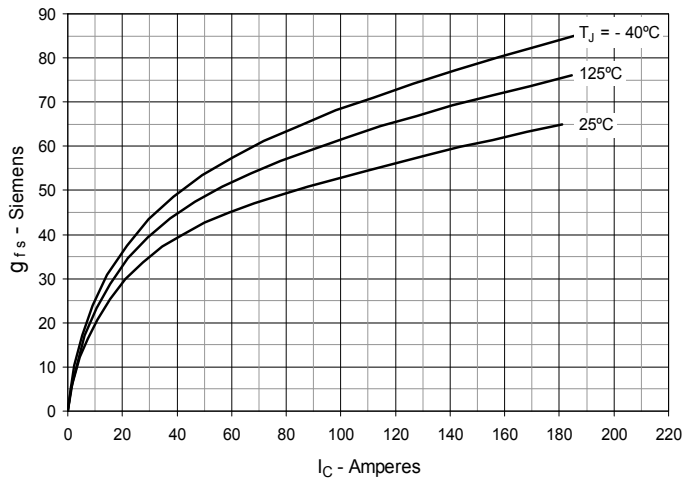
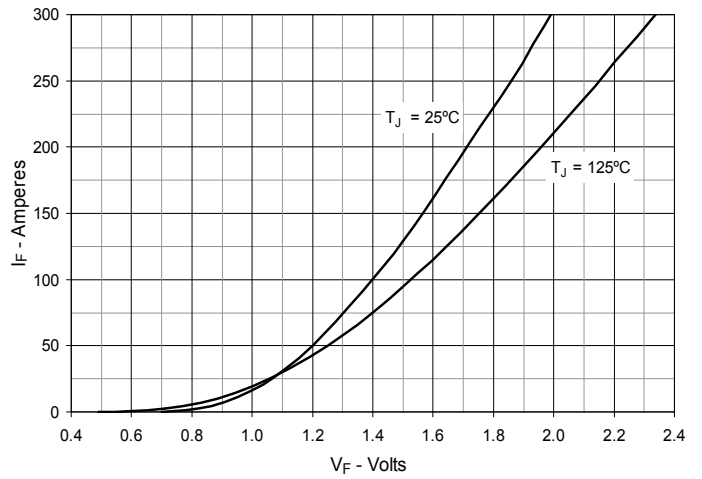
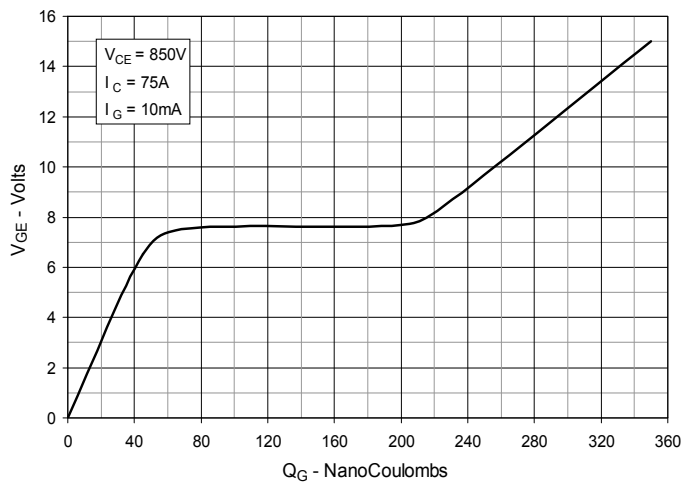
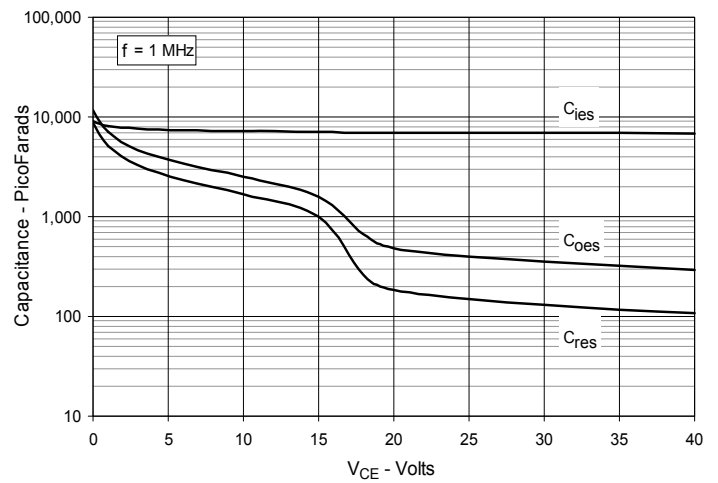
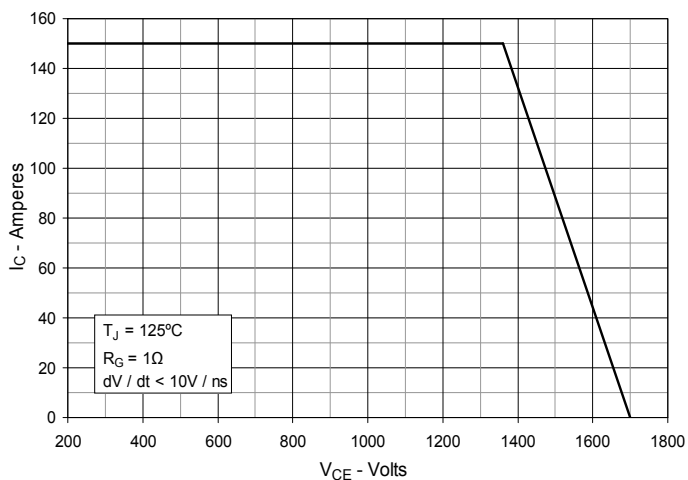
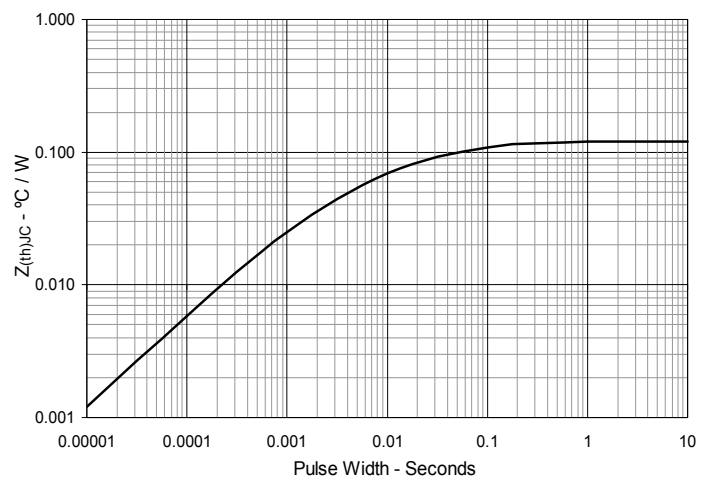
Fig. 7. Transconductance

Fig. 8. Forward Voltage Drop of Intrinsic Diode

Fig. 9. Gate Charge

Fig. 10. Capacitance

Fig. 11. Reverse-Bias Safe Operating Area

Fig. 12. Maximum Transient Thermal Impedance


Fig. 13. Resistive Turn-on Rise Time vs. Junction Temperature

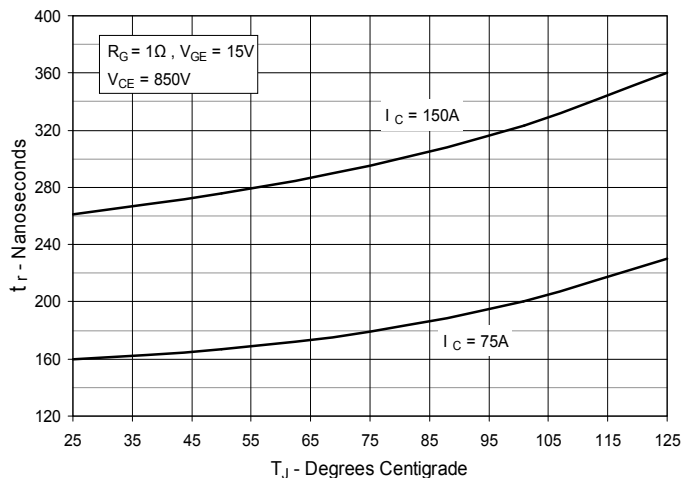


Fig. 14. Resistive Turn-on Rise Time vs. Collector Current

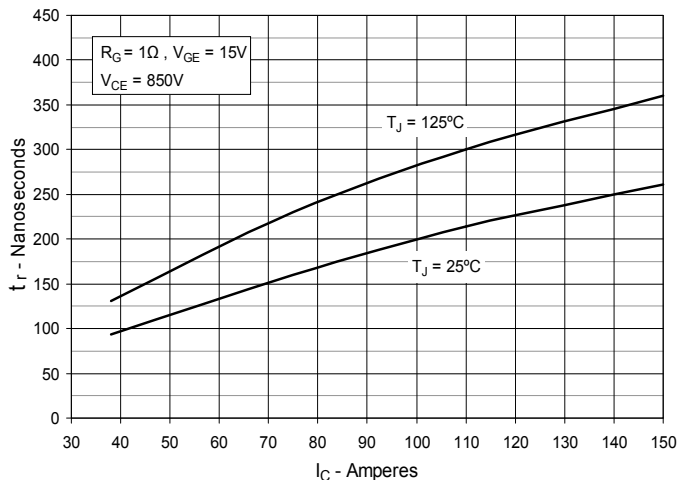


Fig. 15. Resistive Turn-on Switching Times vs. Gate Resistance

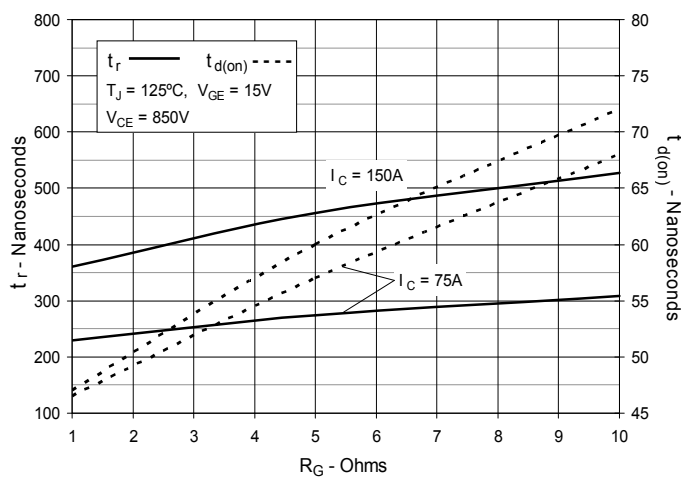


Fig. 16. Resistive Turn-off Switching Times vs. Junction Temperature

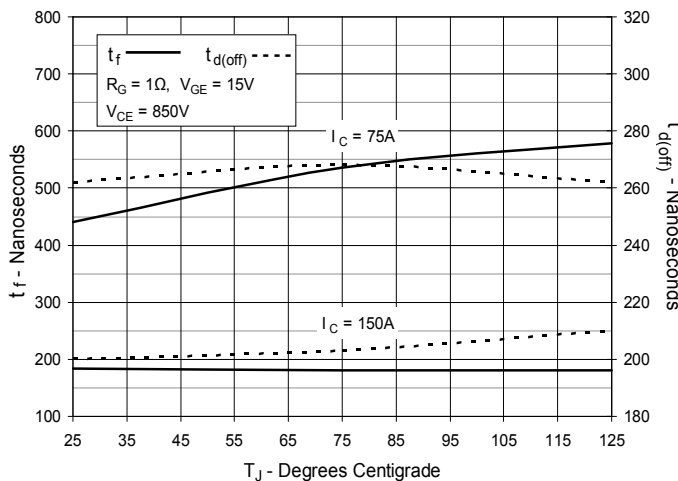


Fig. 17. Resistive Turn-off Switching Times vs. Collector Current

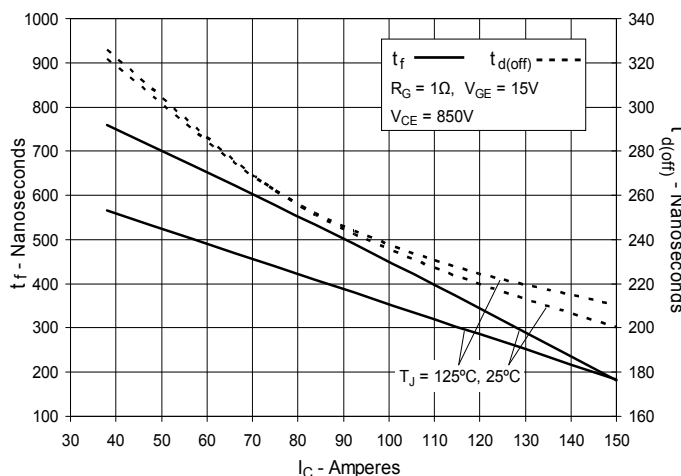


Fig. 18. Resistive Turn-off Switching Times vs. Gate Resistance

